









#### ISO7730, ISO7731

SLLSES0D - SEPTEMBER 2016-REVISED MAY 2017

# ISO773x High-Speed, Robust-EMC Reinforced Triple-Channel Digital Isolators

#### Features 1

- Signaling Rate: Up to 100 Mbps
- Wide Supply Range: 2.25 V to 5.5 V
- 2.25-V to 5.5-V Level Translation
- Default Output High and Low Options
- Wide Temperature Range: -55°C to +125°C
- Low Power Consumption, Typical 1.5 mA per Channel at 1 Mbps
- Low Propagation Delay: 11 ns Typical (5-V Supplies)
- High CMTI: ±100 kV/µs Typical
- Robust Electromagnetic Compatibility (EMC)
  - System-Level ESD, EFT, and Surge Immunity
  - Low Emissions
- Isolation Barrier Life: >40 Years
- Wide-SOIC (DW-16) and QSOP (DBQ-16) Package Options
- Safety-Related Certifications:
  - Reinforced Insulation per DIN V VDE V 0884-10 (VDE V 0884-10):2006-12
  - 5000  $V_{RMS}$  (DW) and 2500  $V_{RMS}$  (DBQ) Isolation Rating per UL 1577
  - CSA Component Acceptance Notice 5A, IEC 60950-1 and IEC 60601-1 End Equipment Standards
  - CQC Certification per GB4943.1-2011
  - TUV Certification according to EN 60950-1 and EN 61010-1
  - Certifications for DW Package Complete; All Other Certifications are Planned

## 2 Applications

- Industrial Automation
- Motor Control
- Power Supplies
- Solar Inverters
- Medical Equipment

## **3** Description

The ISO773x devices are high-performance, triplechannel digital isolators with 5000 V<sub>RMS</sub> (DW package) and 2500 V<sub>RMS</sub> (DBQ package) isolation ratings per UL 1577.

This family of devices has reinforced insulation ratings according to VDE, CSA, TUV and CQC.

The ISO773x family of devices provides high electromagnetic immunity and low emissions at low power consumption, while isolating CMOS or LVCMOS digital I/Os. Each isolation channel has a logic input and output buffer separated by a silicon dioxide (SiO<sub>2</sub>) insulation barrier. This device comes with enable pins which can be used to put the respective outputs in high impedance for multi-master reduce applications and driving to power consumption. The ISO7730 device has all three channels in the same direction and the ISO7731 device has two forward and one reverse-direction channel. If the input power or signal is lost, the default output is high for devices without suffix F and low for devices with suffix F. See the Device Functional Modes section for further details.

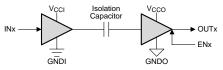
Used in conjunction with isolated power supplies, this device helps prevent noise currents on a data bus or other circuits from entering the local ground and interfering with or damaging sensitive circuitry. Through innovative chip design and layout techniques, electromagnetic compatibility of the ISO773x device has been significantly enhanced to ease system-level ESD, EFT, surge, and emissions compliance. The ISO773x family of devices is available in 16-pin wide-SOIC and QSOP packages.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
ISO7730	SOIC (DW)	10.30 mm × 7.50 mm
ISO7731	SSOP (DBQ)	4.90 mm × 3.90 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

#### **Simplified Schematic**



V<sub>CCI</sub> and GNDI are supply and ground connections, respectively, for the input channels.

V<sub>CCO</sub> and GNDO are supply and ground connections, respectively, for the output channels.



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Page

# **Table of Contents**

1	Feat	ures 1
2	App	lications 1
3	Desc	cription 1
4	Revi	sion History 2
5	Pin (	Configuration and Functions 4
6	Spec	cifications5
	6.1	Absolute Maximum Ratings 5
	6.2	ESD Ratings5
	6.3	Recommended Operating Conditions 5
	6.4	Thermal Information6
	6.5	Power Ratings6
	6.6	Insulation Specifications7
	6.7	Safety-Related Certifications8
	6.8	Safety Limiting Values8
	6.9	Electrical Characteristics—5-V Supply
	6.10	Supply Current Characteristics—5-V Supply9
	6.11	Electrical Characteristics—3.3-V Supply 10
	6.12	
	6.13	
	6.14	Supply Current Characteristics—2.5-V Supply 11
	6.15	Switching Characteristics—5-V Supply 12
	6.16	Switching Characteristics—3.3-V Supply 13
	6.17	Switching Characteristics—2.5-V Supply 13
	6.18	Insulation Characteristics Curves 14

Changes from Revision B (October 2016) to Revision C

	6.19	Typical Characteristics	15
7	Para	meter Measurement Information	17
8	Deta	iled Description	19
	8.1	Overview	19
	8.2	Functional Block Diagram	19
	8.3	Feature Description	20
	8.4	Device Functional Modes	21
9	App	lication and Implementation	22
	9.1	Application Information	22
	9.2	Typical Application	22
10	Pow	er Supply Recommendations	25
11	Lay	out	26
	11.1	Layout Guidelines	26
	11.2	Layout Example	26
12	Dev	ice and Documentation Support	27
	12.1		
	12.2	Related Links	27
	12.3	Receiving Notification of Documentation Updates	27
	12.4	Community Resources	27
	12.5	Trademarks	27
	12.6	Electrostatic Discharge Caution	27
	12.7	Glossary	27
13		hanical, Packaging, and Orderable mation	28

## **4** Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision C (December 2016) to Revision D P	age
•	Updated the Safety-Related Certifications table	8
•	Changed the minimum CMTI from 40 to 85 in all Electrical Characteristics tables	9

•	Changed the Regulatory Information table to Safety-Related Certifications and updated content	8
•	Changed the certifications from planned to certified in the Safety-Related Certifications table	8

Cł	hanges from Revision A (September 2016) to Revision B	Page
•	Changed Feature From: "VDE and UL Certifications" To: "VDE, UL, and TUV Certifications"	1
•	Changed the unit value of CLR and CPG From: µm To: mm in Insulation Specifications	7
•	Changed From: "according to VDE and UL;" To: "according to VDE, UL, and TUV;" in the conditions statement of <i>Safety-Related Certifications</i>	8
•	Changed From: "Plan to certify" To: "Certified" in column TUV of Safety-Related Certifications	8
•	Changed From: "Certification Planned" To: "Certification Planned' to 'Client ID number: 77311" in column TUV of Safety-Related Certifications	8

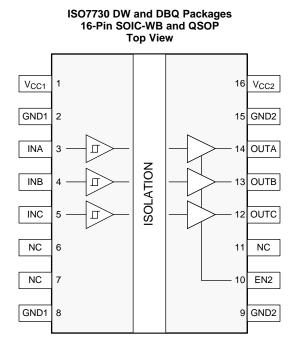


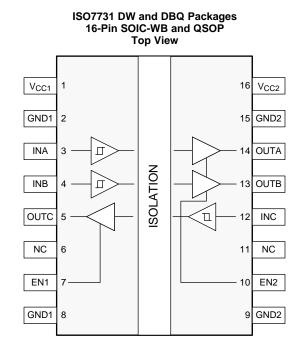
#### Changes from Original (September 2016) to Revision A

Page

•	Changed V <sub>I(HYS)</sub> MIN value From: 0.1 × V <sub>CC0</sub> To: 0.1 × V <sub>CCI</sub> in <i>Electrical Characteristics</i> —5-V Supply	9
•	Changed V <sub>I(HYS)</sub> MIN value From: 0.1 × V <sub>CCO</sub> To: 0.1 × V <sub>CCI</sub> in <i>Electrical Characteristics</i> —3.3-V Supply	10
•	Changed V <sub>I(HYS)</sub> MIN value From: 0.1 × V <sub>CC0</sub> To: 0.1 × V <sub>CC1</sub> in <i>Electrical Characteristics</i> —2.5-V Supply	. 11
•	Changed CMTI MIN value From: 35 To: 40 in <i>Electrical Characteristics</i> -3.3-V Supply	11
•	Changed PWD MAX value From: 4.7 To: 4.9 in Switching Characteristics—5-V Supply	12
•	Changed t <sub>sk(o)</sub> MAX value From: 3.5 To: 4 in Switching Characteristics—5-V Supply	12
•	Changed t <sub>DO</sub> MAX value From: 9 To: 0.3 in Switching Characteristics—5-V Supply	12
•	Changed t <sub>DO</sub> MAX value From: 9 To: 0.3 in Switching Characteristics-3.3-V Supply	13
•	Changed t <sub>DO</sub> MAX value From: 9 To: 0.3 in Switching Characteristics-2.5-V Supply	13
•	Added Note B to Figure 15	18

# 5 Pin Configuration and Functions





#### **Pin Functions**

PIN					
NAME	N	0.	I/O	DESCRIPTION	
	ISO7730	ISO7731			
EN1	—	7	I	Output enable 1. Output pins on side 1 are enabled when EN1 is high or open and in high-impedance state when EN1 is low.	
EN2	10	10	I	Output enable 2. Output pins on side 2 are enabled when EN2 is high or open and in high-impedance state when EN2 is low.	
GND1	2, 8	2, 8	_	Ground connection for $V_{CC1}$	
GND2	9, 15	9, 15	_	Ground connection for $V_{CC2}$	
INA	3	3	I	Input, channel A	
INB	4	4	I	Input, channel B	
INC	5	12	I	Input, channel C	
NC	6, 7, 11	6, 11	_	Not connected	
OUTA	14	14	0	Output, channel A	
OUTB	13	13	0	Output, channel B	
OUTC	12	5	0	Output, channel C	
V <sub>CC1</sub>	1	1	—	Power supply, V <sub>CC1</sub>	
V <sub>CC2</sub>	16	16		Power supply, V <sub>CC2</sub>	

4

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## 6 Specifications

## 6.1 Absolute Maximum Ratings

See  $^{(1)}$ 

		MIN	MAX	UNIT
$V_{CC1}, V_{CC2}$	Supply voltage <sup>(2)</sup>	-0.5	6	V
V	Voltage at INx, OUTx, ENx	-0.5	$V_{CCX} + 0.5^{(3)}$	V
Io	Output current	-15	15	mA
TJ	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values except differential I/O bus voltages are with respect to the local ground terminal (GND1 or GND2) and are peak voltage values.

(3) Maximum voltage must not exceed 6 V.

#### 6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	±6000	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all $\ensuremath{pins^{(2)}}$	±1500	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions

			MIN	NOM	МАХ	UNIT
V <sub>CC1</sub> , V <sub>CC2</sub>	Supply voltage		2.25		5.5	V
V <sub>CC(UVLO+)</sub>	UVLO threshold when supp	ly voltage is rising		2	2.25	V
V <sub>CC(UVLO-)</sub>	UVLO threshold when supp	ly voltage is falling	1.7	1.8		V
V <sub>HYS(UVLO)</sub>	Supply voltage UVLO hyste	resis	100	200		mV
		$V_{CCO}^{(1)} = 5 V$	-4			
I <sub>OH</sub>	High-level output current	V <sub>CCO</sub> = 3.3 V	-2			mA
		V <sub>CCO</sub> = 2.5 V	-1			
	Low-level output current	$V_{CCO} = 5 V$			4	mA
I <sub>OL</sub>		V <sub>CCO</sub> = 3.3 V			2	
		V <sub>CCO</sub> = 2.5 V			1	
V <sub>IH</sub>	High-level input voltage		$0.7 \times V_{CCI}^{(1)}$		V <sub>CCI</sub>	V
VIL	Low-level input voltage		0		0.3 × V <sub>CCI</sub>	V
DR	Data rate		0		100	Mbps
T <sub>A</sub>	Ambient temperature		-55	25	125	°C

(1)  $V_{CCI}$  = Input-side  $V_{CC}$ ;  $V_{CCO}$  = Output-side  $V_{CC}$ .

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#### 6.4 Thermal Information

		ISO	ISO773x		
	THERMAL METRIC <sup>(1)</sup>	DW (SOIC)	DBQ (QSOP)	UNIT	
		16 Pins	16 Pins		
$R_{\thetaJA}$	Junction-to-ambient thermal resistance	81.4	109	°C/W	
R <sub>0JC(top)</sub>	Junction-to-case(top) thermal resistance	44.9	46.8	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	45.9	60.6	°C/W	
ΨЈТ	Junction-to-top characterization parameter	28.1	35.9	°C/W	
ΨЈВ	Junction-to-board characterization parameter	45.5	60	°C/W	
R <sub>0JC(bottom)</sub>	Junction-to-case(bottom) thermal resistance	_		°C/W	

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## 6.5 Power Ratings

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT				
ISO77	ISO7730									
$P_D$	Maximum power dissipation				150	mW				
P <sub>D1</sub>	Maximum power dissipation by side-1	$V_{CC1} = V_{CC2} = 5.5 V$ , T <sub>J</sub> = 150°C, C <sub>L</sub> = 15 pF, input a 50-MHz 50% duty cycle square wave			25	mW				
P <sub>D2</sub>	Maximum power dissipation by side-2				125	mW				
ISO77	/31				·					
PD	Maximum power dissipation				150	mW				
P <sub>D1</sub>	Maximum power dissipation by side-1	$V_{CC1} = V_{CC2} = 5.5 V$ , T <sub>J</sub> = 150°C, C <sub>L</sub> = 15 pF, input a 50-MHz 50% duty cycle square wave			50	mW				
P <sub>D2</sub>	Maximum power dissipation by side-2				100	mW				

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#### 6.6 Insulation Specifications

		TEST CONDITIONS	SPECIF		
	PARAMETER	TEST CONDITIONS	DW-16	DBQ-16	UNIT
CLR	External clearance (1)	Shortest terminal-to-terminal distance through air	>8	>3.7	mm
CPG	External creepage <sup>(1)</sup>	Shortest terminal-to-terminal distance across the package surface	>8	>3.7	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	>21	>21	μm
СТІ	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112; UL 746A	>600	>600	V
	Material group	According to IEC 60664-1	I	Ι	
		Rated mains voltage ≤ 150 V <sub>RMS</sub>	I–IV	I–IV	
		Rated mains voltage ≤ 300 V <sub>RMS</sub>	I–IV	I–III	
	Overvoltage category per IEC 60664-1	Rated mains voltage ≤ 600 V <sub>RMS</sub>	I–IV	n/a	
		Rated mains voltage ≤ 1000 V <sub>RMS</sub>	I–III	n/a	
DIN V	VDE V 0884-10 (VDE V 0884-10):2006-1	2 <sup>(2)</sup>			
V <sub>IORM</sub>	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	1414	566	V <sub>PK</sub>
V <sub>IOWM</sub>	Maximum isolation working voltage	AC voltage; Time dependent dielectric breakdown (TDDB) Test	1000	400	V <sub>RMS</sub>
	ũ ũ	DC Voltage	1414	566	V <sub>DC</sub>
V <sub>IOTM</sub>	Maximum transient isolation voltage	$V_{\text{TEST}} = V_{\text{IOTM}}$ t = 60 s (qualification), t = 1 s (100% production)	8000	3600	V <sub>PK</sub>
V <sub>IOSM</sub>	Maximum surge isolation voltage <sup>(3)</sup>	Test method per IEC 60065, 1.2/50 µs waveform, V <sub>TEST</sub> = 1.6 × V <sub>IOSM</sub> (qualification)	8000	4000	V <sub>PK</sub>
		Method a, After Input/Output safety test subgroup 2/3, $V_{ini} = V_{IOTM}$ , $t_{ini} = 60$ s; $V_{pd(m)} = 1.2 \times V_{IORM}$ , $t_m = 10$ s	≤5	≤5	
q <sub>pd</sub>	Apparent charge <sup>(4)</sup>	Method a, After environmental tests subgroup 1, $V_{ini} = V_{IOTM}$ , $t_{ini} = 60$ s; $V_{pd(m)} = 1.6 \times V_{IORM}$ , $t_m = 10$ s	≤5	≤5	рС
		Method b1; At routine test (100% production) and preconditioning (type test) $V_{ini} = V_{IOTM}$ , $t_{ini} = 1$ s; $V_{pd(m)} = 1.875 \times V_{IORM}$ , $t_m = 1$ s	≤5	≤5	
CIO	Barrier capacitance, input to output <sup>(5)</sup>	$V_{IO} = 0.4 \text{ x sin } (2\pi \text{ft}), \text{ f} = 1 \text{ MHz}$	~0.7	~0.7	pF
		$V_{IO} = 500 \text{ V}, \text{ T}_{A} = 25^{\circ}\text{C}$	>10 <sup>12</sup>	>10 <sup>12</sup>	
R <sub>IO</sub>	Isolation resistance <sup>(5)</sup>	$V_{IO} = 500 \text{ V}, \ 100^{\circ}\text{C} \le \text{T}_{A} \le 125^{\circ}\text{C}$	>10 <sup>11</sup>	>10 <sup>11</sup>	Ω
		V <sub>IO</sub> = 500 V at T <sub>S</sub> = 150°C	>10 <sup>9</sup>	>10 <sup>9</sup>	1
	Pollution degree		2	2	
	Climatic category		55/125/21	55/125/21	
UL 157	77				
V <sub>ISO</sub>	Withstanding isolation voltage	$V_{TEST} = V_{ISO}$ , t = 60 s (qualification), $V_{TEST} = 1.2 \times V_{ISO}$ , t = 1 s (100% production)	5000	2500	V <sub>RMS</sub>

(1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

(2) This coupler is suitable for safe electrical insulation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

(3) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.

(4) Apparent charge is electrical discharge caused by a partial discharge (pd).

(5) All pins on each side of the barrier tied together creating a two-terminal device.

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## 6.7 Safety-Related Certifications

DW package devices are certified. All other certifications are planned.

VDE	CSA	UL	CQC	TUV
Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12	Certified according to CSA Component Acceptance Notice 5A, IEC 60950-1 and IEC 60601-1	Certified according to UL 1577 Component Recognition Program	Certified according to GB 4943.1-2011	Certified according to EN 61010-1:2010 (3rd Ed) and EN 60950-1:2006/A11 :2009/A1:2010/A12:2011/A2 :2013
Maximum transient isolation voltage, 8000 V <sub>PK</sub> (DW-16) and 3600 V <sub>PK</sub> (DBQ-16); Maximum repetitive peak isolation voltage, 1414 V <sub>PK</sub> (DW-16, Reinforced) and 566 V <sub>PK</sub> (DBQ-16); Maximum surge isolation voltage, 8000 V <sub>PK</sub> (DW-16) and 4000 V <sub>PK</sub> (DBQ-16)	Reinforced insulation per CSA 60950-1-07+A1+A2 and IEC 60950-1 2nd Ed., 800 $V_{RMS}$ (DW-16) and 370 $V_{RMS}$ (DBQ-16) max working voltage (pollution degree 2, material group I); 2 MOPP (Means of Patient Protection) per CSA 60601-1:14 and IEC 60601-1 Ed. 3.1, 250 $V_{RMS}$ (DW-16) max working voltage	<b>DW-16:</b> Single protection, 5000 V <sub>RMS</sub> ; <b>DBQ-16:</b> Single protection, 2500 V <sub>RMS</sub>	<b>DW-16:</b> Reinforced Insulation, Altitude ≤ 5000 m, Tropical Climate, 400 V <sub>RMS</sub> maximum working voltage; <b>DBQ-16:</b> Basic Insulation, Altitude ≤ 5000 m, Tropical Climate, 250 V <sub>RMS</sub> maximum working voltage	$\begin{array}{c} 5000 \ V_{RMS} \ (DW-16) \ and \\ 2500 \ V_{RMS} \ (DBQ-16) \\ Reinforced insulation per EN \\ 61010-1:2010 \ (3rd Ed) \ up \ to \\ working \ voltage \ of \ 600 \ V_{RMS} \\ (DW-16) \ and \ 300 \ V_{RMS} \ (DW-16) \ and \\ 2500 \ V_{RMS} \ (DW-16) \ and \\ 2500 \ V_{RMS} \ (DBQ-16) \\ Reinforced insulation per EN \\ 60950- \\ 1:2006/A11:2009/A1:2010/A \\ 12:2011/A2:2013 \ up \ to \\ working \ voltage \ of \ 800 \ V_{RMS} \\ (DW -16) \ and \ 370 \ V_{RMS} \ (DBQ-16) \end{array}$
Certificate number: 40040142	Master contract number: 220991	File number: E181974	Certificate number: CQC15001121716	Client ID number: 77311

## 6.8 Safety Limiting Values

Safety limiting<sup>(1)</sup> intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier potentially leading to secondary system failures.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DW-	16 PACKAGE	•				
		$R_{\theta JA} = 81.4 \text{ °C/W}, V_I = 5.5 \text{ V}, T_J = 150 \text{ °C}, T_A = 25 \text{ °C}, \text{ see Figure 1}$			279	
I <sub>S</sub>	Safety input, output, or supply current	$R_{\theta JA} = 81.4 \text{ °C/W}, V_I = 3.6 \text{ V}, T_J = 150 \text{ °C}, T_A = 25 \text{ °C}, \text{ see Figure 1}$			427	mA
	supply surrout	$R_{\theta JA} = 81.4 \text{ °C/W}, V_I = 2.75 \text{ V}, T_J = 150 \text{ °C}, T_A = 25 \text{ °C}, \text{ see Figure 1}$			558	
$P_S$	Safety input, output, or total power	$R_{\theta JA} = 81.4 \text{ °C/W}, T_J = 150 \text{ °C}, T_A = 25 \text{ °C}, \text{ see Figure 3}$			1536	mW
Τs	Maximum safety temperature				150	°C
DBQ	-16 PACKAGE					
		$R_{\theta JA} = 109.0^{\circ}C/W, V_{I} = 5.5 V, T_{J} = 150^{\circ}C, T_{A} = 25^{\circ}C, \text{ see Figure 2}$			209	
I <sub>S</sub>	Safety input, output, or supply current	$R_{\theta JA} = 109.0 \text{ °C/W}, V_I = 3.6 \text{ V}, T_J = 150 \text{ °C}, T_A = 25 \text{ °C}, \text{ see Figure 2}$			319	mA
	supply current	$R_{\theta JA} = 109.0^{\circ}C/W, V_I = 2.75 V, T_J = 150^{\circ}C, T_A = 25^{\circ}C, \text{ see Figure 2}$			417	
$P_S$	Safety input, output, or total power	$R_{\theta JA} = 109.0^{\circ}C/W$ , $T_J = 150^{\circ}C$ , $T_A = 25^{\circ}C$ , see Figure 4			1147	mW
Τs	Maximum safety temperature				150	°C

(1) The maximum safety temperature is the maximum junction temperature specified for the device. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the *Thermal Information* is that of a device installed on a High-K test board for leaded surface mount packages. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.



## 6.9 Electrical Characteristics—5-V Supply

 $V_{CC1} = V_{CC2} = 5 \text{ V} \pm 10\%$  (over recommended operating conditions unless otherwise noted)

001	002	1 5	,			
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -4 mA; see Figure 13	$V_{CCO}^{(1)} - 0.4$	4.8		V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 4 mA; see Figure 13		0.2	0.4	V
V <sub>IT+(IN)</sub>	Rising input voltage threshold			$0.6 \times V_{CCI}$	$0.7 \times V_{CCI}$	V
V <sub>IT-(IN)</sub>	Falling input voltage threshold		$0.3 \times V_{CCI}$	$0.4 \times V_{CCI}$		V
V <sub>I(HYS)</sub>	Input threshold voltage hysteresis		$0.1 \times V_{CCI}$	$0.2 \times V_{CCI}$		V
I <sub>IH</sub>	High-level input current	V <sub>IH</sub> = V <sub>CCI</sub> <sup>(1)</sup> at INx or ENx			10	μΑ
IIL	Low-level input current	V <sub>IL</sub> = 0 V at INx or ENx	-10			μA
CMTI	Common-mode transient immunity	$V_{I} = V_{CCI} \text{ or } 0 \text{ V}, V_{CM} = 1200 \text{ V}; \text{ see Figure 16}$	85	100		kV/μs
CI	Input Capacitance <sup>(2)</sup>	$V_{I} = V_{CC}/2 + 0.4 \times \sin(2\pi ft), f = 1 \text{ MHz}, V_{CC} = 5 \text{ V}$		2		pF

 $V_{CCI}$  = Input-side  $V_{CC}; \ V_{CCO}$  = Output-side  $V_{CC}.$  Measured from input pin to ground. (1)

(2)

## 6.10 Supply Current Characteristics—5-V Supply

 $V_{CC1} = V_{CC2} = 5 \text{ V} \pm 10\%$  (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	ТҮР	МАХ	UNIT
ISO7730			<u>т</u>				
	EN2 = 0 V; V <sub>I</sub> = V <sub>CC1</sub> (ISO7730);		I <sub>CC1</sub>		1	1.4	mA
Supply current - disable	$V_I = 0 V (ISO7730 \text{ with F suffix})$	V <sub>I</sub> = 0 V (ISO7730 with F suffix)			0.3	0.4	mA
Supply current - disable	EN2 = 0 V; V <sub>1</sub> = 0 V (ISO7730);		I <sub>CC1</sub>		4.3	6	mA
	$V_{I} = V_{CC1}$ (ISO7730 with F suffix)		I <sub>CC2</sub>		0.3	0.4	mA
	$EN2 = V_{CC2}; V_1 = V_{CC1} (ISO7730);$	N2 = V <sub>CC2</sub> ; V <sub>I</sub> = V <sub>CC1</sub> (ISO7730);			1	1.4	mA
Supply current - DC signal	$V_I = 0 V (ISO7730 \text{ with F suffix})$		I <sub>CC2</sub>		1.6	2.5	mA
Supply sufficience Do signal	$EN2 = V_{CC2}; V_1 = 0 V (ISO7730);$		I <sub>CC1</sub>		4.3	6	mA
	$V_I = V_{CC1}$ (ISO7730 with F suffix)	1	I <sub>CC2</sub>		1.8	2.7	mA
		1 Mbps	I <sub>CC1</sub>		2.6	3.7	mA
			I <sub>CC2</sub>		1.9	2.8	mA
Supply current - AC signal	$EN2 = V_{CCI}$ ; All channels switching with	10 Mbps	I <sub>CC1</sub>		2.7	3.8	mA
	square wave clock input; $C_L = 15 \text{ pF}$		I <sub>CC2</sub>		3.3	4.5	mA
		100 Mbps	I <sub>CC1</sub>		3.6	4.6	mA
			I <sub>CC2</sub>		17.5	21	mA
ISO7731			TT				
	EN1 = EN2 = 0 V; $V_{I} = V_{CCI}^{(1)}$ (ISO7731);		I <sub>CC1</sub>		0.8	1.2	mA
Supply current - disable	$v_1 = 0$ v (ISO7731 with F suffix)	V <sub>I</sub> = 0 V (ISO7731 with F suffix)			0.7	1	mA
	EN1 = EN2 = 0 V; $V_1 = 0 V$ (ISO7731);				3	4.3	mA
	$V_{I} = V_{CCI}$ (ISO7731 with F suffix)		I <sub>CC2</sub>		1.8	2.6	mA
	EN1 = EN2 = $V_{CCI}$ ; $V_I = V_{CCI}$ (ISO7731); $V_I = 0 V$ (ISO7731 with F suffix)		I <sub>CC1</sub>		1.3	1.7	mA
Supply current - DC signal			I <sub>CC2</sub>		1.6	2.2	mA
	EN1 = EN2 = $V_{CCI}$ ; $V_I$ = 0 V (ISO7731); $V_I$ = $V_{CCI}$ (ISO7731 with F suffix)		I <sub>CC1</sub>		3.5	5	mA
			I <sub>CC2</sub>		2.8	4.1	mA
		1 Mbps	I <sub>CC1</sub>		2.7	3.4	mA
			I <sub>CC2</sub>		2.3	3.3	mA
Supply current - AC signal	$EN1 = EN2 = V_{CCI}$ ; All channels switching with square wave clock input; $C_L = 15 \text{ pF}$	10 Mbps			3 3.3	4	mA
	$\begin{bmatrix} mar & qaare \\ mar & qaare $		I <sub>CC2</sub>			4.4	mA
		100 Mbps	I <sub>CC1</sub>		8.5	11	mA
		1	I <sub>CC2</sub>		13.1	16	mA

(1)  $V_{CCI}$  = Input-side  $V_{CC}$ 

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## 6.11 Electrical Characteristics—3.3-V Supply

 $V_{CC1} = V_{CC2} = 3.3 \text{ V} \pm 10\%$  (over recommended operating conditions unless otherwise noted)

001	002	1 5	,			
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -2 mA; see Figure 13	$V_{CCO}^{(1)} - 0.3$	3.2		V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 2 mA; see Figure 13		0.1	0.3	V
V <sub>IT+(IN)</sub>	Rising input voltage threshold			$0.6 \times V_{CCI}$	$0.7 \times V_{CCI}$	V
V <sub>IT-(IN)</sub>	Falling input voltage threshold		$0.3 \times V_{CCI}$	$0.4 \times V_{CCI}$		V
V <sub>I(HYS)</sub>	Input threshold voltage hysteresis		$0.1 \times V_{CCI}$	$0.2 \times V_{CCI}$		V
I <sub>IH</sub>	High-level input current	$V_{IH} = V_{CCI}^{(1)}$ at INx or ENx			10	μA
IIL	Low-level input current	V <sub>IL</sub> = 0 V at INx or ENx	-10			μA
СМТІ	Common-mode transient immunity	$V_{I} = V_{CCI} \text{ or } 0 \text{ V}, V_{CM} = 1200 \text{ V}; \text{ see Figure 16}$	85	100		kV/μs

(1)  $V_{CCI}$  = Input-side  $V_{CC}$ ;  $V_{CCO}$  = Output-side  $V_{CC}$ .

## 6.12 Supply Current Characteristics—3.3-V Supply

 $V_{CC1} = V_{CC2} = 3.3 \text{ V} \pm 10\%$  (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	ТҮР	МАХ	UNIT
ISO7730	-		+ +				
	EN2 = 0 V; V <sub>I</sub> = V <sub>CC1</sub> (ISO7730);		I <sub>CC1</sub>		1	1.4	mA
Supply current - disable	$V_I = 0 V$ (ISO7730 with F suffix)		I <sub>CC2</sub>		0.3	0.4	mA
Supply current - disable	EN2 = 0 V; V <sub>I</sub> = 0 V (ISO7730);		I <sub>CC1</sub>		4.3	6	mA
	$V_I = V_{CC1}$ (ISO7730 with F suffix)		I <sub>CC2</sub>		0.3	0.4	mA
	EN2 = V <sub>CC2</sub> ; V <sub>I</sub> = V <sub>CC1</sub> (ISO7730);		I <sub>CC1</sub>		1	1.4	mA
Supply current - DC signal	$V_1 = 0 V$ (ISO7730 with F suffix)		I <sub>CC2</sub>		1.6	2.5	mA
oupply our one Do signal	EN2 = V <sub>CC2</sub> ; V <sub>I</sub> = 0 V (ISO7730);		I <sub>CC1</sub>		4.3	6	mA
	$V_{I} = V_{CC1}$ (ISO7730 with F suffix)		I <sub>CC2</sub>		1.8	2.7	mA
		1 Mbps	I <sub>CC1</sub>		2.6	3.7	mA
			I <sub>CC2</sub>		1.8	2.8	mA
Supply current - AC signal	EN2 = V <sub>CCI</sub> ; All channels switching with	10 Mbps	I <sub>CC1</sub>		2.7	3.8	mA
Supply Surrow No Signal	square wave clock input; $C_L = 15 \text{ pF}$		I <sub>CC2</sub>		2.8	3.9	mA
		100 Mbps	I <sub>CC1</sub>		3.3	4.3	mA
			I <sub>CC2</sub>		13	17	mA
IS07731							
	$EN1 = EN2 = 0 V; V_I = V_{CCI}^{(1)} (ISO7731);$		I <sub>CC1</sub>		0.8	1.2	mA
Supply current - disable	V <sub>I</sub> = 0 V (ISO7731 with F suffix)		I <sub>CC2</sub>		0.7	1	mA
	EN1 = EN2 = 0 V; V <sub>1</sub> = 0 V (ISO7731);		I <sub>CC1</sub>		3	4.3	mA
	$V_{I} = V_{CCI}$ (ISO7731 with F suffix)		I <sub>CC2</sub>		1.8	2.6	mA
	$EN1 = EN2 = V_{CCI}; V_I = V_{CCI} (ISO7731);$		I <sub>CC1</sub>		1.3	1.7	mA
Supply current - DC signal	V <sub>I</sub> = 0 V (ISO7731 with F suffix)		I <sub>CC2</sub>		1.6	2.2	mA
Cuppiy current De cignal	$EN1 = EN2 = V_{CCI}; V_I = 0 V (ISO7731);$		I <sub>CC1</sub>		3.5	5	mA
	$V_{I} = V_{CCI}$ (ISO7731 with F suffix)	-	I <sub>CC2</sub>		2.8	4.1	mA
		1 Mbps	I <sub>CC1</sub>		2.4	3.4	mA
			I <sub>CC2</sub>		2.2	3.3	mA
Supply current - AC signal	$EN1 = EN2 = V_{CCI}$ ; All channels switching	10 Mbps	I <sub>CC1</sub>		2.8	3.8	mA
erer, surrent i te signal	with square wave clock input; $C_L = 15 \text{ pF}$		I <sub>CC2</sub>		2.9	4	mA
		100 Mbps	I <sub>CC1</sub>		6.7	8.5	mA
			I <sub>CC2</sub>		10	12.5	mA

(1)  $V_{CCI}$  = Input-side  $V_{CC}$ 



## 6.13 Electrical Characteristics—2.5-V Supply

 $V_{CC1} = V_{CC2} = 2.5 \text{ V} \pm 10\%$  (over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -1 mA; see Figure 13	$V_{CCO}^{(1)} - 0.2$	2.45		V			
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 1 mA; see Figure 13		0.05	0.2	V			
V <sub>IT+(IN)</sub>	Rising input voltage threshold			$0.6 \times V_{CCI}$	$0.7 \times V_{CCI}$	V			
V <sub>IT-(IN)</sub>	Falling input voltage threshold		$0.3 \times V_{CCI}$	$0.4 \times V_{CCI}$		V			
V <sub>I(HYS)</sub>	Input threshold voltage hysteresis		$0.1 \times V_{CCI}$	$0.2 \times V_{CCI}$		V			
I <sub>IH</sub>	High-level input current	$V_{IH} = V_{CCI}^{(1)}$ at INx or ENx			10	μA			
IIL	Low-level input current	V <sub>IL</sub> = 0 V at INx or ENx	-10			μA			
CMTI	Common-mode transient immunity	$V_I = V_{CCI} \text{ or } 0 \text{ V}, V_{CM} = 1200 \text{ V}; \text{ see Figure 16}$	85	100		kV/μs			

(1)  $V_{CCI}$  = Input-side  $V_{CC}$ ;  $V_{CCO}$  = Output-side  $V_{CC}$ .

## 6.14 Supply Current Characteristics—2.5-V Supply

 $V_{CC1} = V_{CC2} = 2.5 \text{ V} \pm 10\%$  (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISO7730						u	
	EN2 = 0 V; V <sub>I</sub> = V <sub>CC1</sub> (ISO7730);		I <sub>CC1</sub>		1	1.4	mA
Supply current - disable	$V_I = 0 V (ISO7730 \text{ with F suffix})$		I <sub>CC2</sub>		0.3	0.4	mA
Supply current - disable	EN2 = 0 V; V <sub>I</sub> = 0 V (ISO7730);		I <sub>CC1</sub>		4.3	6	mA
	$V_I = V_{CC1}$ (ISO7730 with F suffix)		I <sub>CC2</sub>		0.3	0.4	mA
	EN2 = V <sub>CC2</sub> ; V <sub>I</sub> = V <sub>CC1</sub> (ISO7730);		I <sub>CC1</sub>		1	1.4	mA
Supply current - DC signal	$V_I = 0 V$ (ISO7730 with F suffix)		I <sub>CC2</sub>		1.6	2.5	mA
Supply current - DC signal	EN2 = V <sub>CC2</sub> ; V <sub>I</sub> = 0 V (ISO7730);		I <sub>CC1</sub>		4.3	6	mA
	$V_{I} = V_{CC1}$ (ISO7730 with F suffix)		I <sub>CC2</sub>		1.8	2.7	mA
		1 Mbps	I <sub>CC1</sub>		2.6	3.7	mA
		Timps	I <sub>CC2</sub>		1.8	2.7	mA
Supply current - AC signal	EN2 = $V_{CC2}$ ; All channels switching with	10 Mbps	I <sub>CC1</sub>		2.6	3.8	mA
Supply current - AC Signal	square wave clock input; $C_L = 15 \text{ pF}$	TO Mops	I <sub>CC2</sub>		2.5	3.6	mA
		100 Mbps	I <sub>CC1</sub>		3.1	4.2	mA
		100 Mbps	I <sub>CC2</sub>		10.2	14	mA
ISO7731							
	EN1 = EN2 = 0 V; V <sub>I</sub> = V <sub>CCI</sub> <sup>(1)</sup> (ISO7731);		I <sub>CC1</sub>		0.8	1.2	mA
Supply current - disable	$V_I = 0 V (ISO7731 \text{ with F suffix})$		I <sub>CC2</sub>		0.7	1	mA
Supply current - disable	EN1 = EN2 = 0 V; V <sub>1</sub> = 0 V (ISO7731);	EN1 = EN2 = 0 V; V <sub>1</sub> = 0 V (ISO7731);			3	4.3	mA
	$V_I = V_{CCI}$ (ISO7731 with F suffix)		I <sub>CC2</sub>		1.8	2.6	mA
	EN1 = EN2 = V <sub>CCI</sub> ; V <sub>I</sub> = V <sub>CCI</sub> (ISO7731);		I <sub>CC1</sub>		1.3	1.7	mA
Supply current - DC signal	$V_I = 0 V (ISO7731 \text{ with F suffix})$		I <sub>CC2</sub>		1.6	2.2	mA
Supply current - DC signal	EN1 = EN2 = V <sub>CCI</sub> ; V <sub>I</sub> = 0 V (ISO7731);		I <sub>CC1</sub>		3.5	5	mA
	$V_I = V_{CCI}$ (ISO7731 with F suffix)		I <sub>CC2</sub>		2.8	4.1	mA
		1 Mbps	I <sub>CC1</sub>		2.4	3.4	mA
		i winhe	I <sub>CC2</sub>		2.2	3.2	mA
Supply current - AC signal	EN1 = EN2 = V <sub>CCI</sub> ; All channels switching	10 Mbps	I <sub>CC1</sub>		2.7	3.7	mA
Suppry current - AC signal	with square wave clock input; $C_L = 15 \text{ pF}$		I <sub>CC2</sub>		2.7	3.8	mA
		100 Mbps	I <sub>CC1</sub>		5.6	7	mA
		100 Mbps			8	10	mA

(1)  $V_{CCI}$  = Input-side  $V_{CC}$ 

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## 6.15 Switching Characteristics—5-V Supply

 $V_{CC1} = V_{CC2} = 5 \text{ V} \pm 10\%$  (over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay time	0 Figure 40	6	11	16	ns
PWD	Pulse width distortion <sup>(1)</sup>  t <sub>PHL</sub> - t <sub>PLH</sub>	See Figure 13		0.6	4.9	ns
t <sub>sk(o)</sub>	Channel-to-channel output skew time <sup>(2)</sup>	Same-direction channels			4	ns
t <sub>sk(pp)</sub>	Part-to-part skew time <sup>(3)</sup>				4.5	ns
t <sub>r</sub>	Output signal rise time	See Figure 12		1.3	3.9	ns
t <sub>f</sub>	Output signal fall time	See Figure 13		1.4	3.9	ns
t <sub>PHZ</sub>	Disable propagation delay, high-to-high impedance output			8	20	ns
t <sub>PLZ</sub>	Disable propagation delay, low-to-high impedance output			8	20	ns
	Enable propagation delay, high impedance-to-high output for ISO773x	_		7	20	ns
t <sub>PZH</sub>	Enable propagation delay, high impedance-to-high output for ISO773x with F suffix	See Figure 14		3	8.5	μS
	Enable propagation delay, high impedance-to-low output for ISO773x			3	8.5	μS
t <sub>PZL</sub>	Enable propagation delay, high impedance-to-low output for ISO773x with F suffix			7	20	ns
t <sub>DO</sub>	Default output delay time from input power loss	Measured from the time $V_{CC}$ goes below 1.7 V. See Figure 15		0.1	0.3	μS
t <sub>ie</sub>	Time interval error	2 <sup>16</sup> – 1 PRBS data at 100 Mbps		0.6		ns

(1) Also known as pulse skew.

(2) t<sub>sk(0)</sub> is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

(3) t<sub>sk(pp)</sub> is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.



## 6.16 Switching Characteristics—3.3-V Supply

V<sub>CC1</sub> = V<sub>CC2</sub> = 3.3 V ±10% (over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay time	Ora Firme 12	6	11	16	ns
PWD	Pulse width distortion <sup>(1)</sup>  t <sub>PHL</sub> - t <sub>PLH</sub>	- See Figure 13		0.1	5	ns
t <sub>sk(o)</sub>	Channel-to-channel output skew time <sup>(2)</sup>	Same-direction channels			4.1	ns
t <sub>sk(pp)</sub>	Part-to-part skew time <sup>(3)</sup>				4.5	ns
t <sub>r</sub>	Output signal rise time	Ora Firme 40		1.3	3	ns
t <sub>f</sub>	Output signal fall time	- See Figure 13		1.3	3	ns
t <sub>PHZ</sub>	Disable propagation delay, high-to-high impedance output			17	30	ns
t <sub>PLZ</sub>	Disable propagation delay, low-to-high impedance output	See Figure 14		17	30	ns
	Enable propagation delay, high impedance-to-high output for ISO773x			17	30	ns
t <sub>PZH</sub>	Enable propagation delay, high impedance-to-high output for ISO773x with F suffix			3.2	8.5	μS
	Enable propagation delay, high impedance-to-low output for ISO773x			3.2	8.5	μS
PZL	Enable propagation delay, high impedance-to-low output for ISO773x with F suffix			17	30	ns
t <sub>DO</sub>	Default output delay time from input power loss	Measured from the time $V_{CC}$ goes below 1.7 V. See Figure 15		0.1	0.3	μs
t <sub>ie</sub>	Time interval error	2 <sup>16</sup> – 1 PRBS data at 100 Mbps		0.6		ns

(1) Also known as Pulse Skew.

(2) t<sub>sk(0)</sub> is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

(3) t<sub>sk(pp)</sub> is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

## 6.17 Switching Characteristics—2.5-V Supply

 $V_{CC1} = V_{CC2} = 2.5 \text{ V} \pm 10\%$  (over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay time	See Figure 12	7.5	12	18.5	ns
PWD	Pulse width distortion <sup>(1)</sup>  t <sub>PHL</sub> - t <sub>PLH</sub>	See Figure 13		0.2	5.1	ns
t <sub>sk(o)</sub>	Channel-to-channel output skew time <sup>(2)</sup>	Same-direction Channels			4.1	ns
t <sub>sk(pp)</sub>	Part-to-part skew time <sup>(3)</sup>				4.6	ns
t <sub>r</sub>	Output signal rise time	Con Firmer 40		1	3.5	ns
t <sub>f</sub>	Output signal fall time	See Figure 13		1	3.5	ns
t <sub>PHZ</sub>	Disable propagation delay, high-to-high impedance output			22	40	ns
t <sub>PLZ</sub>	Disable propagation delay, low-to-high impedance output			22	40	ns
t <sub>PZH</sub>	Enable propagation delay, high impedance-to-high output for ISO773x			18	40	ns
	Enable propagation delay, high impedance-to-high output for ISO773x with F suffix	See Figure 14		3.3	8.5	μS
	Enable propagation delay, high impedance-to-low output for ISO773x	_		3.3	8.5	μS
t <sub>PZL</sub>	Enable propagation delay, high impedance-to-low output for ISO773x with F suffix			18	40	ns
t <sub>DO</sub>	Default output delay time from input power loss	Measured from the time $V_{CC}$ goes below 1.7 V. See Figure 15		0.1	0.3	μS
t <sub>ie</sub>	Time interval error	2 <sup>16</sup> – 1 PRBS data at 100 Mbps		0.6		ns

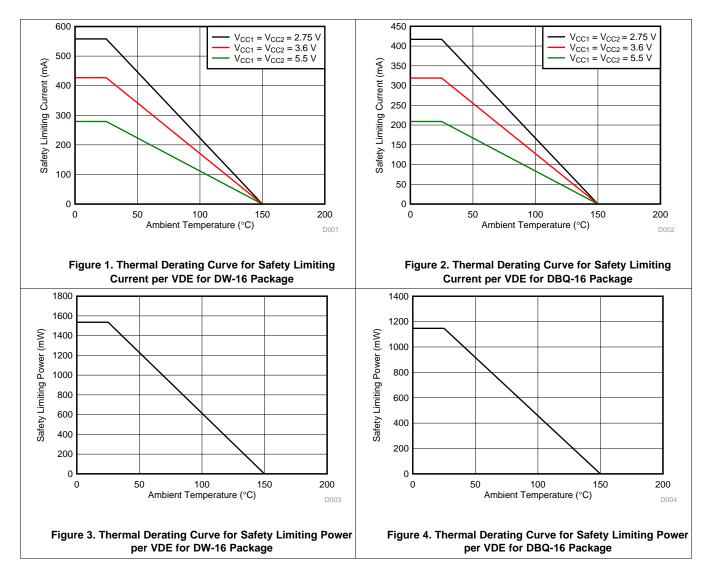
(1) Also known as pulse skew.

(2) t<sub>sk(0)</sub> is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

(3) t<sub>sk(pp)</sub> is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.



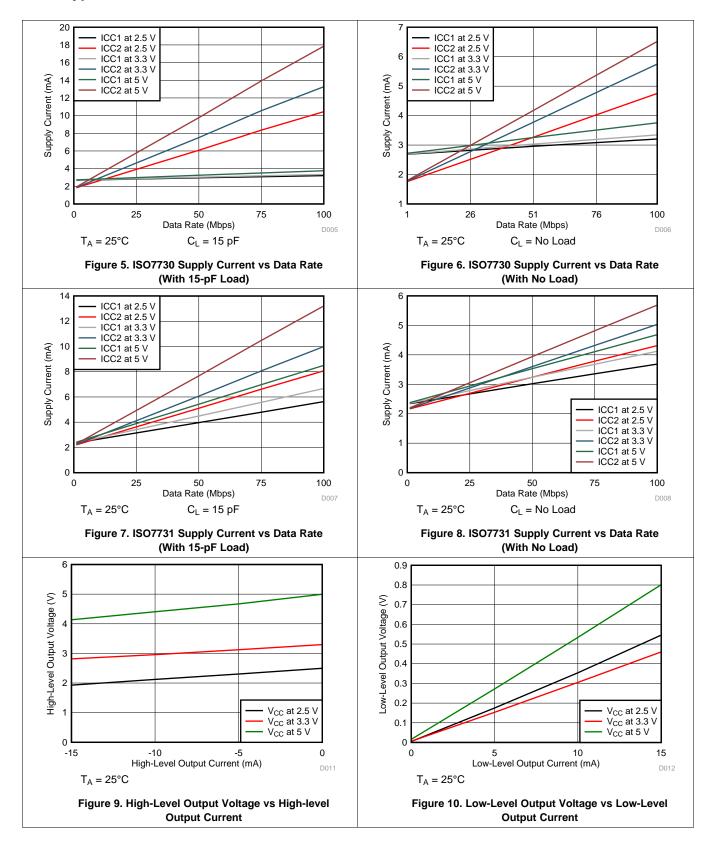
#### 6.18 Insulation Characteristics Curves



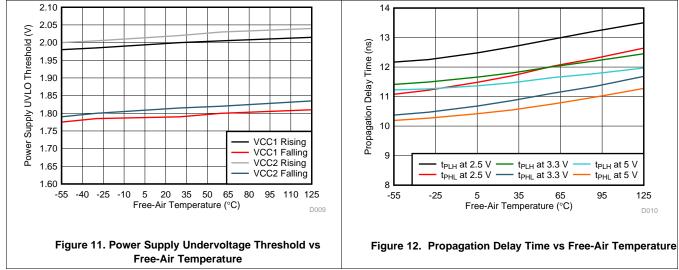
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#### 6.19 Typical Characteristics



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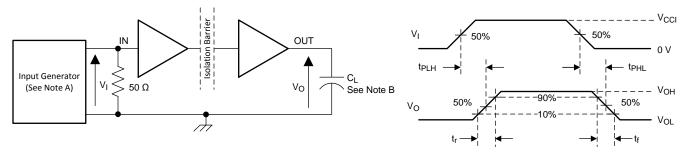


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16

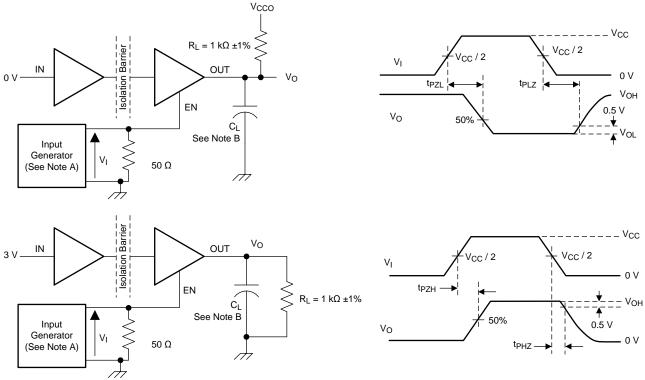


#### 7 Parameter Measurement Information



- A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  50 kHz, 50% duty cycle, t<sub>r</sub>  $\leq$  3 ns, t<sub>f</sub>  $\leq$  3ns, Z<sub>O</sub> = 50  $\Omega$ . At the input, 50  $\Omega$  resistor is required to terminate Input Generator signal. It is not needed in actual application.
- B.  $C_L = 15 \text{ pF}$  and includes instrumentation and fixture capacitance within ±20%.





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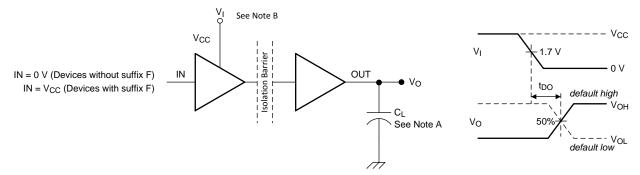
- A. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 10 kHz, 50% duty cycle,  $t_r \le 3$  ns,  $t_f \le 3$  ns,  $Z_0 = 50 \Omega$ .
- B.  $C_L = 15 \text{ pF}$  and includes instrumentation and fixture capacitance within ±20%.

#### Figure 14. Enable/Disable Propagation Delay Time Test Circuit and Waveform

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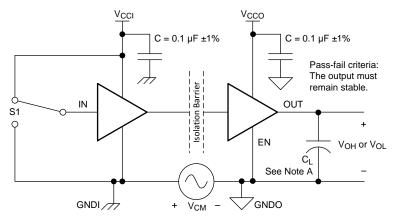
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#### Parameter Measurement Information (continued)



- A.  $C_L = 15 \text{ pF}$  and includes instrumentation and fixture capacitance within ±20%.
- B. Power Supply Ramp Rate = 10 mV/ns

#### Figure 15. Default Output Delay Time Test Circuit and Voltage Waveforms



A.  $C_L = 15 \text{ pF}$  and includes instrumentation and fixture capacitance within ±20%.

Figure 16. Common-Mode Transient Immunity Test Circuit

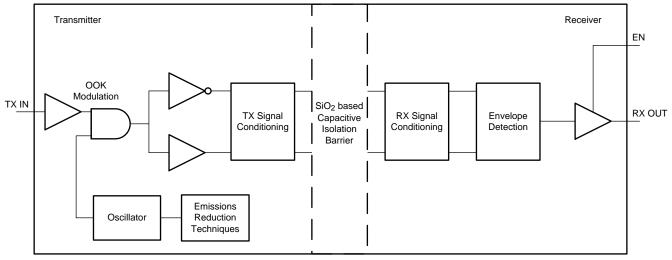


## 8 Detailed Description

#### 8.1 Overview

The ISO773x family of devices has an ON-OFF keying (OOK) modulation scheme to transmit the digital data across a silicon dioxide based isolation barrier. The transmitter sends a high frequency carrier across the barrier to represent one digital state and sends no signal to represent the other digital state. The receiver demodulates the signal after advanced signal conditioning and produces the output through a buffer stage. If the ENx pin is low then the output goes to high impedance. The ISO773x family of devices also incorporates advanced circuit techniques to maximize the CMTI performance and minimize the radiated emissions due the high frequency carrier and IO buffer switching. The conceptual block diagram of a digital capacitive isolator, Figure 17, shows a functional block diagram of a typical channel.

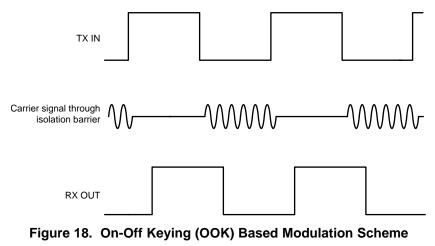
## 8.2 Functional Block Diagram



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Figure 17. Conceptual Block Diagram of a Digital Capacitive Isolator

Figure 18 shows a conceptual detail of how the ON-OFF keying scheme works.



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#### 8.3 Feature Description

Table 1 provides an overview of the device features.

PART NUMBER	CHANNEL DIRECTION	MAXIMUM DATA RATE	DEFAULT OUTPUT	PACKAGE	RATED ISOLATION <sup>(1)</sup>
ISO7730	3 Forward,	100 Mbps	High	DW-16	5000 V <sub>RMS</sub> / 8000 V <sub>PK</sub>
1307730	0 Reverse		riign	DBQ-16	2500 V <sub>RMS</sub> / 3600 V <sub>PK</sub>
ISO7730 with F	3 Forward, 0 Reverse	100 Mbps	Low	DW-16	5000 V <sub>RMS</sub> / 8000 V <sub>PK</sub>
suffix			Low	DBQ-16	2500 V <sub>RMS</sub> / 3600 V <sub>PK</sub>
ISO7731	2 Forward,	100 Mbps	High	DW-16	5000 V <sub>RMS</sub> / 8000 V <sub>PK</sub>
1507731	1 Reverse	sqaw oor	пıgn	DBQ-16	2500 V <sub>RMS</sub> / 3600 V <sub>PK</sub>
ISO7731 with F	2 Forward,	100 Mbps	Low	DW-16	5000 V <sub>RMS</sub> / 8000 V <sub>PK</sub>
suffix	1 Reverse		Low	DBQ-16	2500 V <sub>RMS</sub> / 3600 V <sub>PK</sub>

Table 1. Device Features

(1) See Safety-Related Certifications for detailed isolation ratings.

#### 8.3.1 Electromagnetic Compatibility (EMC) Considerations

Many applications in harsh industrial environment are sensitive to disturbances such as electrostatic discharge (ESD), electrical fast transient (EFT), surge and electromagnetic emissions. These electromagnetic disturbances are regulated by international standards such as IEC 61000-4-x and CISPR 22. Although system-level performance and reliability depends, to a large extent, on the application board design and layout, the ISO773x family of devices incorporates many chip-level design improvements for overall system robustness. Some of these improvements include:

- Robust ESD protection cells for input and output signal pins and inter-chip bond pads.
- Low-resistance connectivity of ESD cells to supply and ground pins.
- Enhanced performance of high voltage isolation capacitor for better tolerance of ESD, EFT and surge events.
- Bigger on-chip decoupling capacitors to bypass undesirable high energy signals through a low impedance path.
- PMOS and NMOS devices isolated from each other by using guard rings to avoid triggering of parasitic SCRs.
- Reduced common mode currents across the isolation barrier by ensuring purely differential internal operation.



#### 8.4 Device Functional Modes

Table 2 lists the functional modes for the ISO773x devices.

V <sub>cci</sub>	v <sub>cco</sub>	INPUT (INx) <sup>(2)</sup>	OUTPUT ENABLE (ENx)	OUTPUT (OUTx)	COMMENTS
		н	H or open	н	Normal Operation:
		L	H or open	L	A channel output assumes the logic state of its input.
PU	PU	Open	H or open	Default	Default mode: When INx is open, the corresponding channel output goes to its default logic state. Default is <i>High</i> for ISO773x and <i>Low</i> for ISO773x with F suffix.
Х	PU	Х	L	Z	A low value of Output Enable causes the outputs to be high-impedance
PD	PU	x	H or open	Default	Default mode: When $V_{CCI}$ is unpowered, a channel output assumes the logic state based on the selected default option. Default is <i>High</i> for IISO773x and <i>Low</i> for ISO773x with F suffix. When $V_{CCI}$ transitions from unpowered to powered-up, a channel output assumes the logic state of its input. When $V_{CCI}$ transitions from powered-up to unpowered, channel output assumes the selected default state.
х	PD	х	x	Undetermined	When $V_{CCO}$ is unpowered, a channel output is undetermined <sup>(3)</sup> . When $V_{CCO}$ transitions from unpowered to powered-up, a channel output assumes the logic state of its input

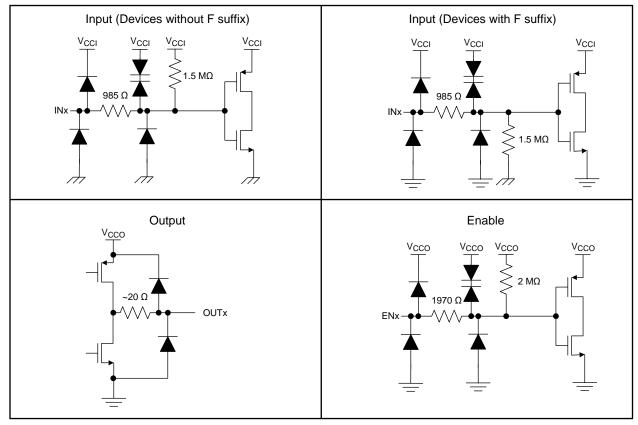
#### Table 2. Function Table<sup>(1)</sup>

 $V_{CCI}$  = Input-side  $V_{CC}$ ;  $V_{CCO}$  = Output-side  $V_{CC}$ ; PU = Powered up ( $V_{CC} \ge 2.25$  V); PD = Powered down ( $V_{CC} \le 1.7$  V); X = Irrelevant; H = High level; L = Low level ; Z = High Impedance A strongly driven input signal can weakly power the floating  $V_{CC}$  via an internal protection diode and cause undetermined output. The outputs are in undetermined state when 1.7 V <  $V_{CCI}$ ,  $V_{CCO}$  < 2.25 V. (1)

(2)

(3)

#### 8.4.1 Device I/O Schematics



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#### Figure 19. Device I/O Schematics

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## 9 Application and Implementation

#### NOTE

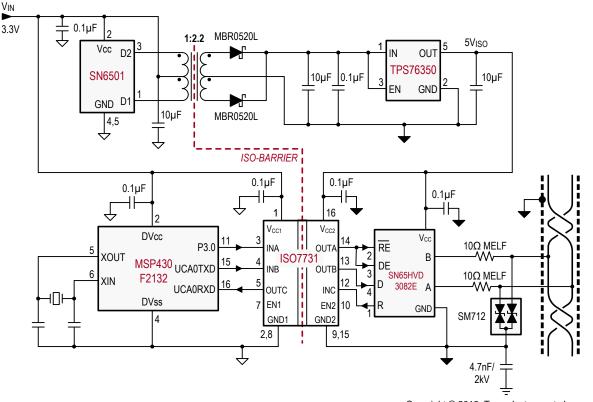
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 9.1 Application Information

The ISO773x devices are high-performance, triple-channel digital isolators. These devices come with enable pins on each side which can be used to put the respective outputs in high impedance for multi-master driving applications and reduce power consumption. The ISO773x family of devices use single-ended CMOS-logic switching technology. The voltage range is from 2.25 V to 5.5 V for both supplies,  $V_{CC1}$  and  $V_{CC2}$ . When designing with digital isolators, keep in mind that because of the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (that is,  $\mu$ C or UART), and a data converter or a line transceiver, regardless of the interface type or standard.

#### 9.2 Typical Application

The ISO7731 device, combined with Texas Instruments' mixed-signal microcontroller, RS-485 transceiver, transformer driver, and voltage regulator, can create an isolated RS-485 system as shown in Figure 20.



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#### **Typical Application (continued)**

#### 9.2.1 Design Requirements

To design with these devices, use the parameters listed in Table 3.

PARAMETER	VALUE
Supply voltage, $V_{CC1}$ and $V_{CC2}$	2.25 to 5.5 V
Decoupling capacitor between V <sub>CC1</sub> and GND1	0.1 μF
Decoupling capacitor from V <sub>CC2</sub> and GND2	0.1 μF

#### 9.2.2 Detailed Design Procedure

Unlike optocouplers, which require external components to improve performance, provide bias, or limit current, the ISO773x family of devices only requires two external bypass capacitors to operate. Figure 21 and Figure 22 show the typical circuit hook-up for the devices.

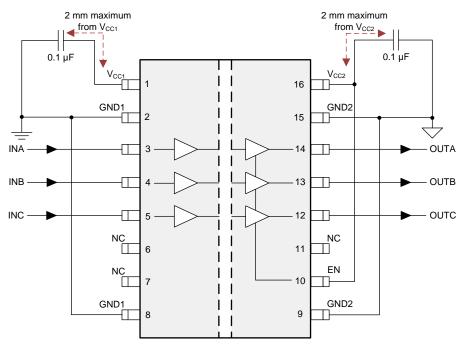


Figure 21. Typical ISO7730 Circuit Hook-Up



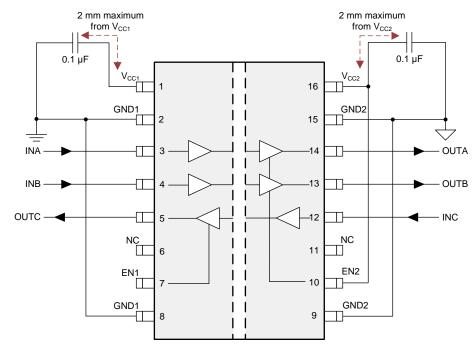
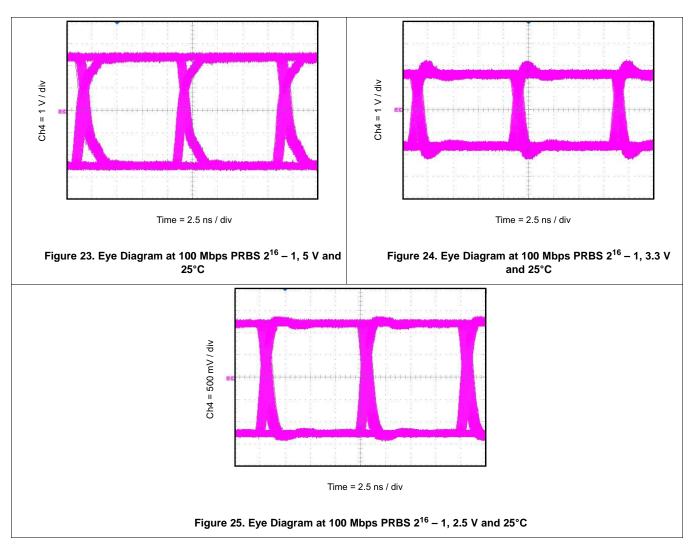


Figure 22. Typical ISO7731 Circuit Hook-Up



#### 9.2.3 Application Curves

The following typical eye diagrams of the ISO773x family of devices indicate low jitter and wide open eye at the maximum data rate of 100 Mbps.



## **10** Power Supply Recommendations

To help ensure reliable operation at data rates and supply voltages, a  $0.1-\mu$ F bypass capacitor is recommended at the input and output supply pins (V<sub>CC1</sub> and V<sub>CC2</sub>). The capacitors should be placed as close to the supply pins as possible. If only a single primary-side power supply is available in an application, isolated power can be generated for the secondary-side with the help of a transformer driver such as Texas Instruments' SN6501 or SN6505A. For such applications, detailed power supply design and transformer selection recommendations are available in the SN6501 Transformer Driver for Isolated Power Supplies (SLLSEA0) or SN6505A Low-Noise 1-A Transformer Drivers for Isolated Power Supplies (SLLSEP9).



## 11 Layout

#### 11.1 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see Figure 26). Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/inch<sup>2</sup>.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

If an additional supply voltage plane or signal layer is needed, add a second power or ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

For detailed layout recommendations, refer to the *Digital Isolator Design Guide* (SLLA284).

#### 11.1.1 PCB Material

For digital circuit boards operating below 150 Mbps, (or rise and fall times higher than 1 ns), and trace lengths of up to 10 inches, use standard FR-4 UL94V-0 printed circuit boards. This PCB is preferred over cheaper alternatives due to its lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and self-extinguishing flammability-characteristics.

#### 11.2 Layout Example

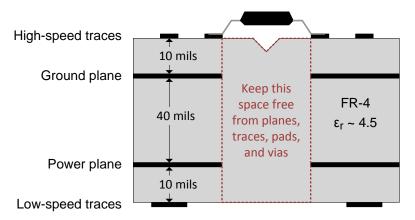


Figure 26. Layout Example Schematic



## **12 Device and Documentation Support**

#### **12.1** Documentation Support

#### 12.1.1 Related Documentation

For related documentation, see the following:

- Digital Isolator Design Guide (SLLA284)
- Isolation Glossary (SLLA353)
- SN6501 Transformer Driver for Isolated Power Supplies (SLLSEA0)
- SNx5HVD308xE Low-Power RS-485 Transceivers, Available in a Small MSOP-8 Package (SLLS562)
- TPS76350 Low-Power 150-mA Low-Dropout Linear Regulators (SLVS181)
- MSP430F2132 Mixed Signal Microcontroller (SLAS578)

#### 12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

PARTS	PRODUCT FOLDER	ORDER NOW	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY	
ISO7730	Click here	Click here	Click here	Click here	Click here	
ISO7731	Click here	Click here	Click here	Click here	Click here	

#### Table 4. Related Links

#### 12.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### **12.4 Community Resources**

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E<sup>™</sup> Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support TI's Design Support** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.5 Trademarks

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#### 12.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 12.7 Glossary

#### SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.



## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



EXAS

**ISTRUMENTS** 

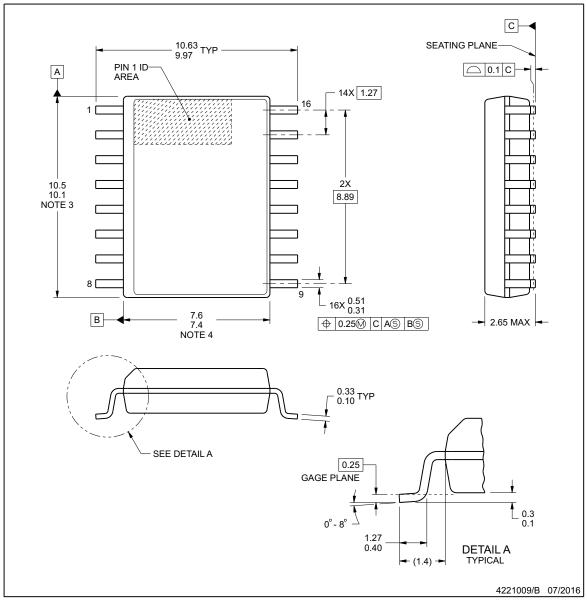
**DW0016B** 



## PACKAGE OUTLINE

#### SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- 5. Reference JEDEC registration MS-013.

Texas Instruments

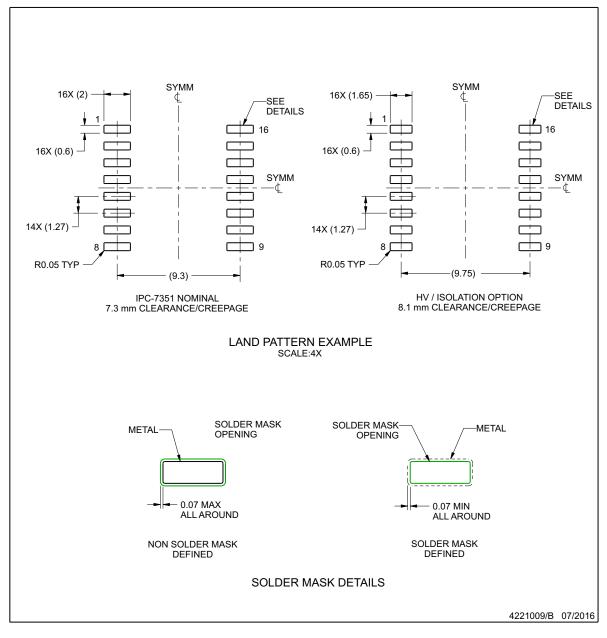
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## **EXAMPLE BOARD LAYOUT**

# DW0016B

## SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



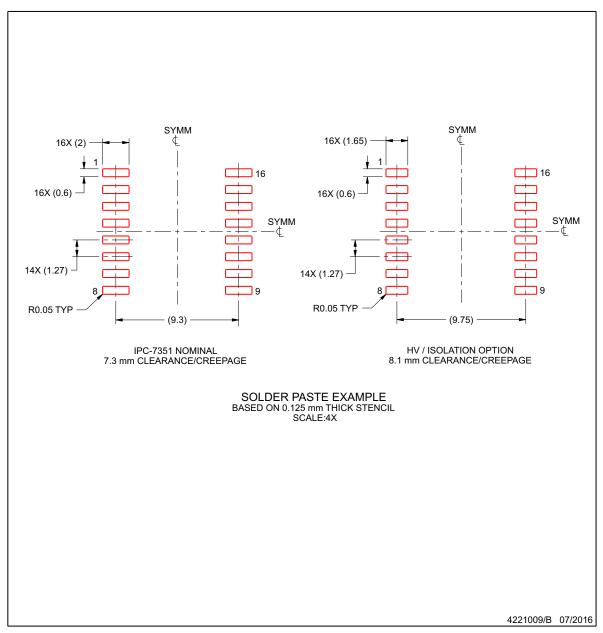
**DW0016B** 

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## **EXAMPLE STENCIL DESIGN**

#### SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations. 9. Board assembly site may have different recommendations for stencil design.



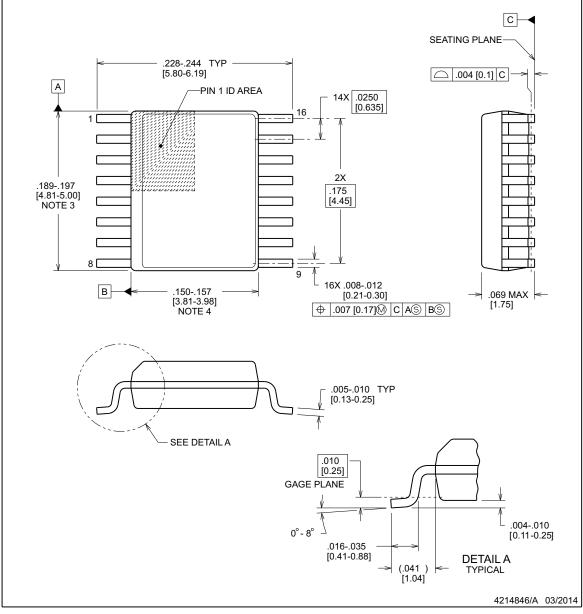
# States

# DBQ0016A

## PACKAGE OUTLINE

#### SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



NOTES:

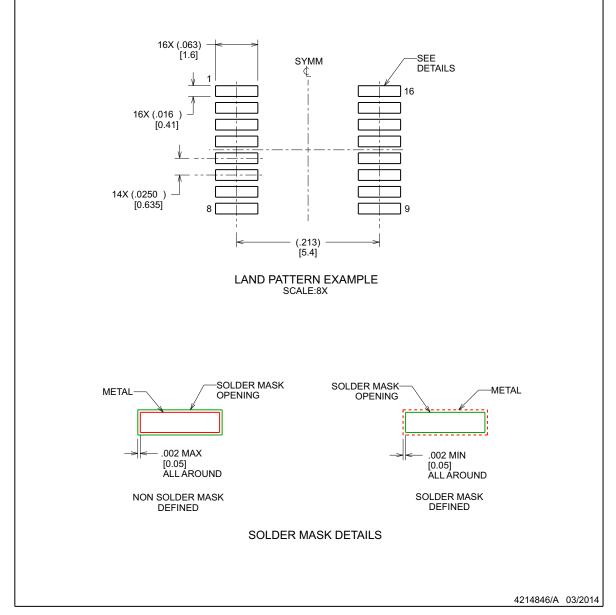
- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed .006 inch, per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MO-137, variation AB.

#### ISO7730, ISO7731 SLLSES0D - SEPTEMBER 2016 - REVISED MAY 2017

# **EXAMPLE BOARD LAYOUT**

#### SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

#### XAS **ISTRUMENTS**

# **DBQ0016A**

**DBQ0016A** 

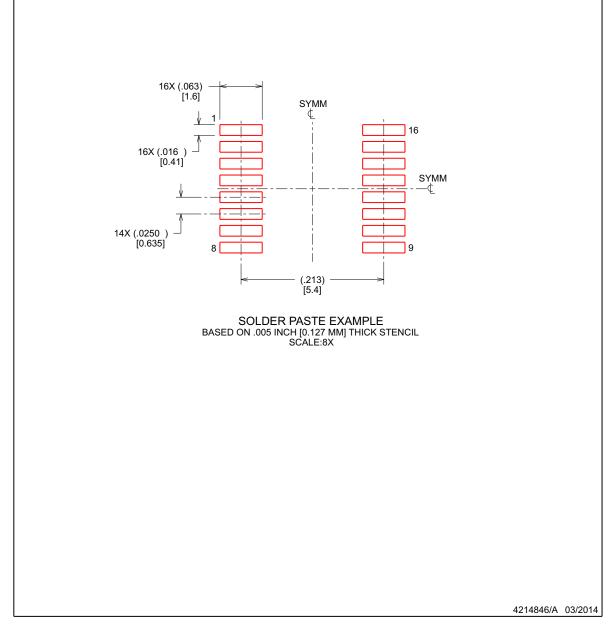


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## **EXAMPLE STENCIL DESIGN**

#### SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.

34



24-May-2017

## **PACKAGING INFORMATION**

Orderable Device	Status	Package Type		Pins	0	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
ISO7730DBQ	PREVIEW	SSOP	DBQ	16	75	Green (RoHS & no Sb/Br)	Call TI	Level-2-260C-1 YEAR	-55 to 125	7730	
ISO7730DBQR	PREVIEW	SSOP	DBQ	16	2500	TBD	Call TI	Call TI	-55 to 125	7730	
ISO7730DW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7730	Samples
ISO7730DWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7730	Samples
ISO7730FDBQ	PREVIEW	SSOP	DBQ	16	75	Green (RoHS & no Sb/Br)	Call TI	Level-2-260C-1 YEAR	-55 to 125	7730F	
ISO7730FDBQR	PREVIEW	SSOP	DBQ	16	2500	TBD	Call TI	Call TI	-55 to 125	7730F	
ISO7730FDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7730F	Samples
ISO7730FDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7730F	Samples
ISO7731DBQ	PREVIEW	SSOP	DBQ	16	75	Green (RoHS & no Sb/Br)	Call TI	Level-2-260C-1 YEAR	-55 to 125	7731	
ISO7731DBQR	PREVIEW	SSOP	DBQ	16	2500	TBD	Call TI	Call TI	-55 to 125	7731	
ISO7731DW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7731	Samples
ISO7731DWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7731	Samples
ISO7731FDBQ	PREVIEW	SSOP	DBQ	16	75	Green (RoHS & no Sb/Br)	Call TI	Level-2-260C-1 YEAR	-55 to 125	7731F	
ISO7731FDBQR	PREVIEW	SSOP	DBQ	16	2500	TBD	Call TI	Call TI	-55 to 125	7731F	
ISO7731FDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7731F	Samples
ISO7731FDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7731F	Samples

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.



24-May-2017

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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#### OTHER QUALIFIED VERSIONS OF ISO7730, ISO7731 :

• Automotive: ISO7730-Q1, ISO7731-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

# PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



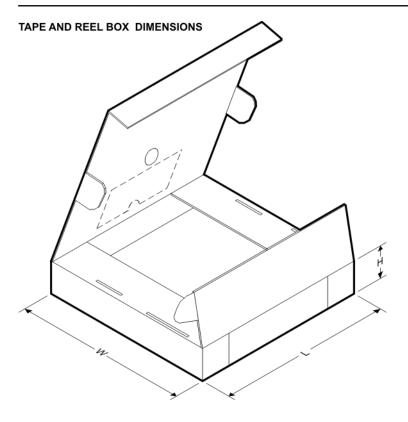
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7730DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7730FDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7731DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7731FDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

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# PACKAGE MATERIALS INFORMATION

26-Apr-2017



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7730DWR	SOIC	DW	16	2000	367.0	367.0	38.0
ISO7730FDWR	SOIC	DW	16	2000	367.0	367.0	38.0
ISO7731DWR	SOIC	DW	16	2000	367.0	367.0	38.0
ISO7731FDWR	SOIC	DW	16	2000	367.0	367.0	38.0

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